

SD57045

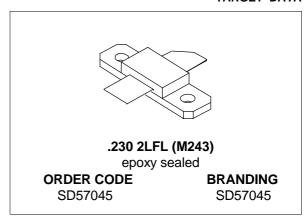
RF & MICROWAVE TRANSISTORS N-Channel Enhancement-Mode Lateral MOSFETs

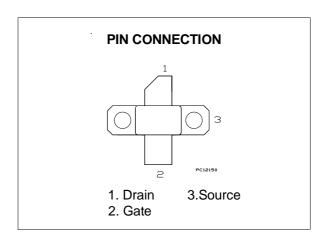
TARGET DATA

- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION
- P_{OUT} = 45 W PEP with 13 dB gain @ 945 MHz
- BeO FREE PACKAGE

DESCRIPTION

The SD57045 is a common source N-Channel enhancement-mode lateral Field-Effect RF power transistor designed for broadband commercial and industrial applications at frequencies up to 1.0 GHz. The SD57045 is designed for high gain and broadband performance operating in common source mode at 28V. It is ideal for base stations applications requiring high linearity.





ABSOLUTE MAXIMUM RATINGS (T_{case} = 25 °C)

Symbol	Parameter	Value	Unit
V _{(BR)DSS}	Drain Source Voltage	65	V
V_{DGR}	Drain-Gate Voltage ($R_{GS} = 1 M\Omega$)	65	V
V_{GS}	Gate-Source Voltage	± 20	V
I_{D}	Drain Current	5	Α
P _{DISS}	Power Dissipation (@ Tc= 70 °C)	93	W
Tj	Max. Operating Junction Temperature	200	O°
T _{STG}	Storage Temperature	-65 to 200	°C

THERMAL DATA

R _{th(j-c)} Junction-Case Thermal Resistance	1.4	°C/W	
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ELECTRICAL SPECIFICATION $(T_{case} = 25 \, {}^{o}C)$

STATIC

Symbol		Parameter		Min.	Тур.	Max.	Unit
$V_{(BR)DSS}$	$V_{GS} = 0V$	$I_{DS} = 1 \text{ mA}$		65			٧
I _{DSS}	$V_{GS} = 0V$	$V_{DS} = 28 V$				1	μΑ
I_{GSS}	V _{GS} = 20V	$V_{DS} = 0 V$	V _{DS} = 0 V			1	μΑ
$V_{GS(Q)}$	V _{DS} = 28V	$I_D = 250 \text{ mA}$		2.5		5.0	٧
$V_{DS(ON)}$	$V_{GS} = 10V$	$I_D = 3 A$			0.7		٧
G_FS	V _{DS} = 10V	$I_D = 5 A$			2.7		mho
C _{ISS}	V _{GS} = 0V	$V_{DS} = 28 \text{ V}$	f = 1 MHz		80		pF
C_{OSS}	$V_{GS} = 0V$	$V_{DS} = 28 V$	f = 1 MHz		40		pF
C _{RSS}	$V_{GS} = 0V$	$V_{DS} = 28 \text{ V}$	f = 1 MHz		3.2		pF

DYNAMIC

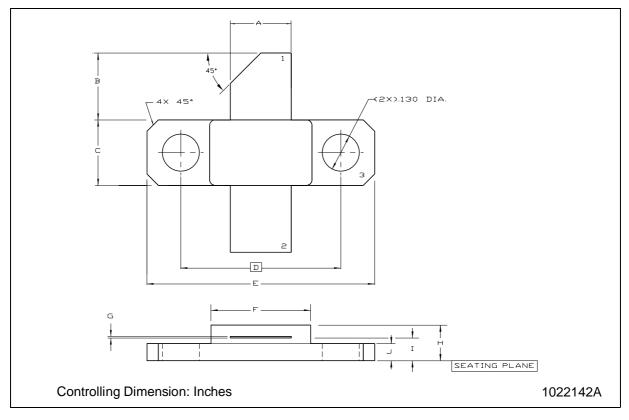
Symbol	Parameter	Min.	Тур.	Max.	Unit
Pout	$f = 945 \text{ MHz}$ $V_{DD} = 28V$ $I_{DQ} = 250 \text{ mA}$	45			W
IMD ₃	$V_{DD} = 28 \text{ V}$ $P_{out} = 45 \text{ W PEP}$ $I_{DQ} = 250 \text{ mA}$		-32	-28	dBc
G _{PS}	$V_{DD} = 28 \text{ V}$ $P_{out} = 45 \text{ W PEP}$ $I_{DQ} = 250 \text{ mA}$	13	15		dB
η _D	$V_{DD} = 28 \text{ V}$ $P_{out} = 45 \text{ W PEP}$ $I_{DQ} = 250 \text{ mA}$	33	40		%
Load Mismatch	$f = 945 \text{ MHz} V_{DD} = 28 \text{ V} \qquad P_{out} = 45 \text{ W} \qquad I_{DQ} = 250 \text{ mA}$ ALL PHASE ANGLES	5:1			VSWR

Note: $f_1 = 945.0 \text{ MHz}$ $f_2 = 945.1 \text{ MHz}$

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M243 MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	5.21		5.72	0.205		0.225	
В	5.46		6.48	0.215		0.255	
С	5.59		6.10	0.220		0.240	
D		14.27			0.562		
Е	20.07		20.57	0.790		0.810	
F	8.89		9.40	0.350		0.370	
G	0.10		0.15	0.004		0.006	
Н	3.18		4.45	0.125		0.175	
I	1.78		2.29	0.070		0.090	
J	1.27		1.78	0.050		0.070	



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